



JCS15N65EI

主要参数MAIN CHARACTERISTICS

I_D	15A
V_{DS}	650V
$R_{DS(on)-max}$ ($V_{GS}=10V$)	0.52 Ω
Q_g-Typ	52.3nC

用途

- 高频开关电源
- 电子镇流器
- LED 电源

APPLICATIONS

- High efficiency switch mode power supplies
- Electronic lamp ballasts based on half bridge
- LED power supplies

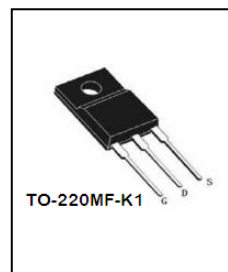
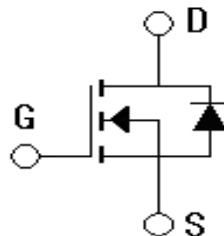
产品特性

- 低栅极电荷
- 开关速度快
- 产品全部经过雪崩测试
- 高抗 dv/dt 能力
- RoHS 产品

FEATURES

- Low gate charge
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes				印记 Marking	封装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen-Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen-Free-Reel		
JCS15N65FEI-F1-B	JCS15N65FEI-F1-BR	N/A	N/A	JCS15N65F	TO-220MF-K1



绝对最大额定值ABSOLUTE RATINGS($T_c=25^{\circ}\text{C}$)

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
最高漏极-源极直流电压 Drain-Source Voltage	V_{DSS}	650	V
连续漏极电流 Drain Current-continuous	I_D $T=25^{\circ}\text{C}$ $T=100^{\circ}\text{C}$	15	A
		9	A
最大脉冲漏极电流 (注1) Drain Current – pulse (note 1)	I_{DM}	60	A
最高栅源电压 Gate-Source Voltage	V_{GSS}	± 30	V
单脉冲雪崩能量 (注2) Single Pulsed Avalanche Energy (note 2)	E_{AS}	640	mJ
最大电压变化速率 MOSFET dv/dt ruggedness	dv/dt	290	V/ns
二极管反向恢复最大电压变化速率 (注3) Peak Diode Recovery dv/dt (note 3)		0.676	
耗散功率 Power Dissipation	P_D $T_c=25^{\circ}\text{C}$ -Derate above 25°C	43.8	W
		0.35	W/ $^{\circ}\text{C}$
最高结温及存储温度 Operating and Storage Temperature Range	T_J, T_{STG}	150; $-55 \sim +150$	$^{\circ}\text{C}$
引线最高焊接温度 Maximum Lead Temperature for Soldering Purposes	T_L	300	$^{\circ}\text{C}$

*漏极电流由最高结温限制

*Drain current limited by maximum junction temperature



电特性 ELECTRICAL CHARACTERISTICS

项目 Parameter	符号 Symbol	测试条件 Tests conditions	最小 Min	典型 Typ	最大 Max	单位 Units
关态特性 Off –Characteristics						
漏—源击穿电压 Drain-Source Voltage	BV_{DSS}	$I_D=250\mu A, V_{GS}=0V$	650	-	-	V
击穿电压温度特性 Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	$I_D=250\mu A$, referenced to 25°C	-	0.65	-	V/°C
零栅压下漏极漏电流 Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V, V_{GS}=0V, T_C=25^\circ C$	-	-	1	μA
		$V_{DS}=520V, V_{GS}=0V, T_C=125^\circ C$	-	-	100	μA
正向栅极体漏电流 Gate-body leakage current, forward	I_{GSSF}	$V_{DS}=0V, V_{GS}=30V$	-	-	100	nA
反向栅极体漏电流 Gate-body leakage current, reverse	I_{GSSR}	$V_{DS}=0V, V_{GS}=-30V$	-	-	-100	nA
通态特性 On-Characteristics						
阈值电压 Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D=250\mu A$	2.5	-	4.5	V
静态导通电阻 Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=7.5A$ 25°C	-	0.48	0.52	Ω
		$V_{GS}=10V, I_D=7.5A$ 100°C	-	0.85	0.95	Ω
		$V_{GS}=10V, I_D=7.5A$ 150°C	-	1.2	1.3	Ω
正向跨导 Forward Transconductance	g_{fs}	$V_{DS}=40V, I_D=7.5A$ (note 4)	-	12.7	-	S
动态特性 Dynamic Characteristics						
栅极电阻 Gate resistance	R_g	$F=1.0MHz$ open drain	1	2.5	4.0	Ω
输入电容 Input capacitance	C_{iss}	$V_{DS}=25V,$ $V_{GS}=0V,$ $f=1.0MHz$	-	2160	-	pF
输出电容 Output capacitance	C_{oss}		-	198	-	pF
反向传输电容 Reverse transfer capacitance	C_{rss}		-	28	-	pF





电特性 ELECTRICAL CHARACTERISTICS

开关特性 Switching Characteristics						
延迟时间 Turn-On delay time	t _{d(on)}	V _{DD} =325V,I _D =7.5A,R _G =25Ω (note 4, 5)	-	40	-	ns
上升时间 Turn-On rise time	t _r		-	65	-	ns
延迟时间 Turn-Off delay time	t _{d(off)}		-	131	-	ns
下降时间 Turn-Off Fall time	t _f		-	55	-	ns
栅极电荷总量 Total Gate Charge	Q _g	V _{DS} =520V ,	-	52.3	-	nC
栅-源电荷 Gate-Source charge	Q _{gs}	I _D =7.5A	-	15	-	nC
栅-漏电荷 Gate-Drain charge	Q _{gd}	V _{GS} =10V (note 4, 5)	-	20.7	-	nC
漏-源二极管特性及最大额定值 Drain-Source Diode Characteristics and Maximum Ratings						
正向最大连续电流 Maximum Continuous Drain -Source Diode Forward Current	I _S		-	-	15	A
正向最大脉冲电流 Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}		-	-	60	A
正向压降 Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =15A	-	-	1.40	V
反向恢复时间 Reverse recovery time	t _{rr}	V _{GS} =0V, I _S =15A	-	463	-	ns
反向恢复电荷 Reverse recovery charge	Q _{rr}	dI _F /dt=100A/μs (note 4)	-	5.6	-	μC

热特性 THERMAL CHARACTERISTIC

项目 Parameter	符号 Symbol	数值 Value	单位 Unit
结到管壳的热阻 Thermal Resistance, Junction to Case	$R_{th(j-c)}$	2.85	$^{\circ}C/W$
结到环境的热阻 Thermal Resistance, Junction to Ambient	$R_{th(j-A)}$	45.5	$^{\circ}C/W$

注释:

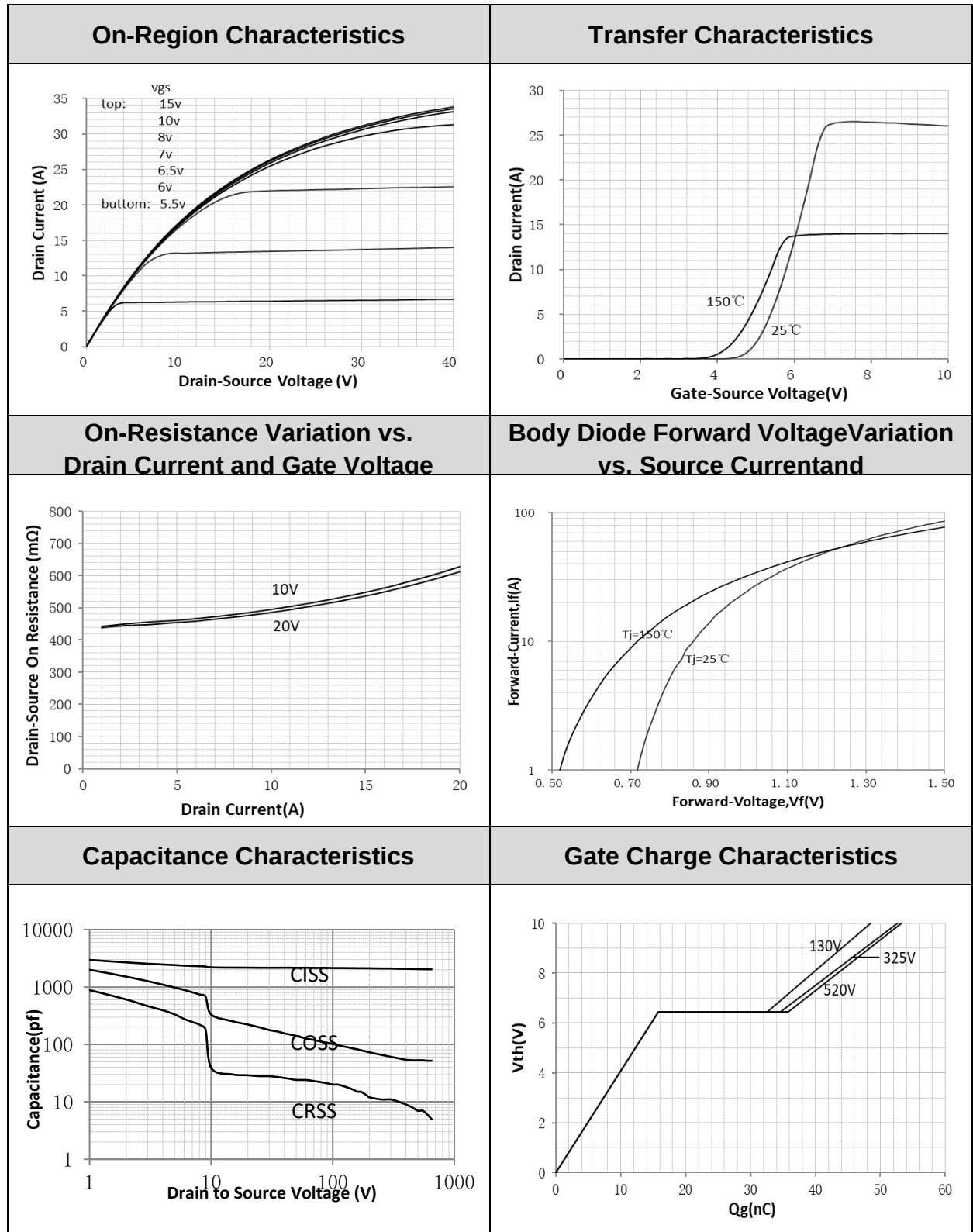
- 1: 脉冲宽度由最高结温限制
- 2: $L=5mH, I_{AS}=16A, V_{DD}=50V, R_G=25\Omega$, 起始结温 $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 20A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, 起始结温 $T_J=25^{\circ}C$
- 4: 脉冲测试: 脉冲宽度 $\leq 300\mu s$, 占空比 $\leq 2\%$
- 5: 基本与工作温度无关

Notes:

- 1: Pulse width limited by maximum junction temperature
- 2: $L=5mH, I_{AS}=16A, V_{DD}=50V, R_G=25\Omega$, Starting $T_J=25^{\circ}C$
- 3: $I_{SD} \leq 20A, di/dt \leq 300A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J=25^{\circ}C$
- 4: Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycles $\leq 2\%$
- 5: Essentially independent of operating temperature

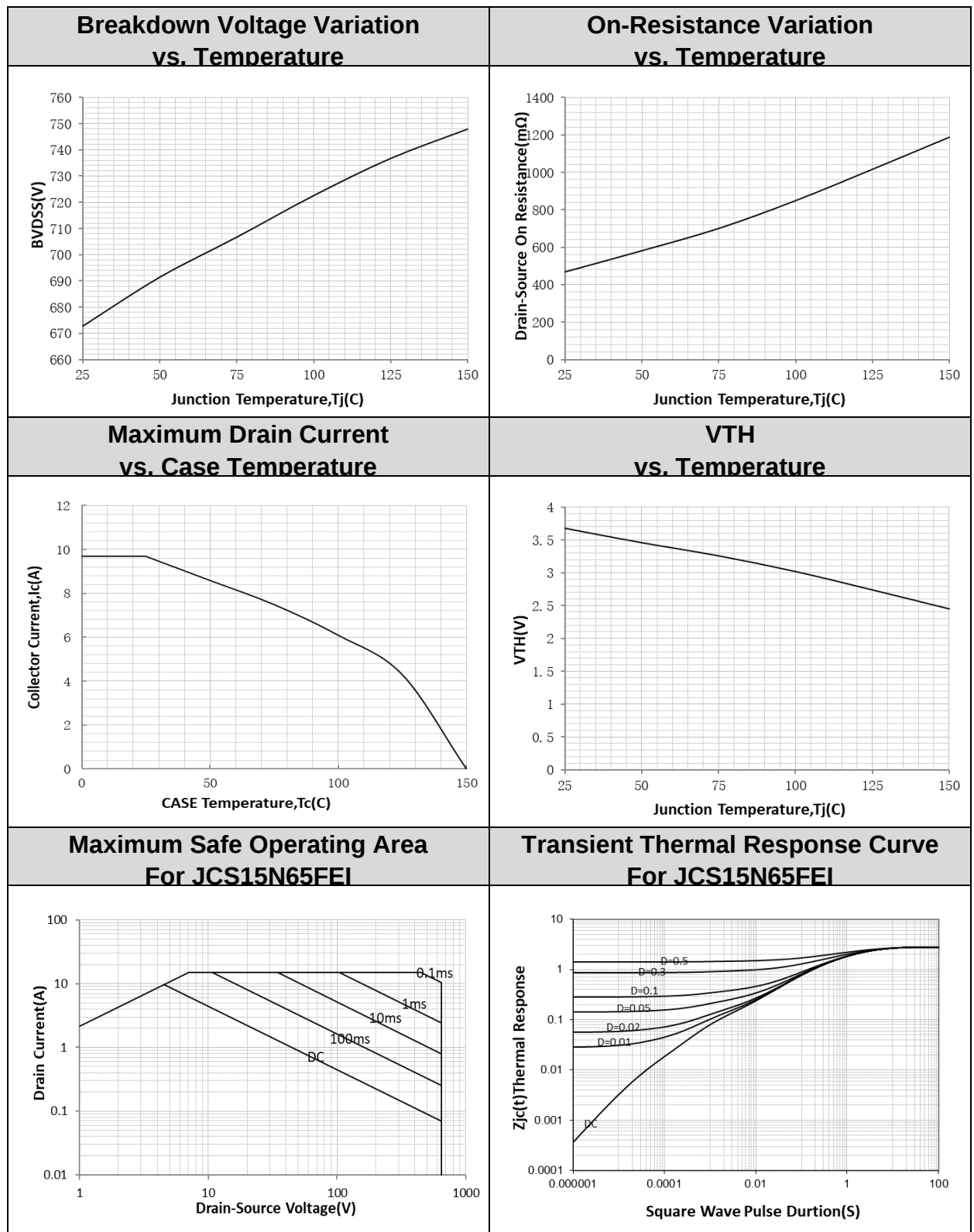


特征曲线ELECTRICAL CHARACTERISTICS (curves)





特征曲线ELECTRICAL CHARACTERISTICS (curves)

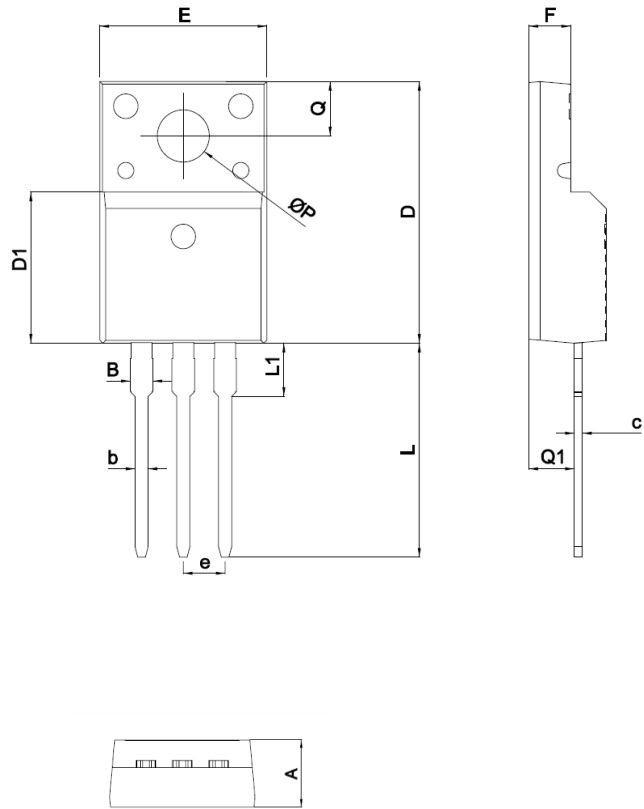




外形尺寸 PACKAGE MECHANICAL DATA

TO-220MF-K1

单位 Unit: mm



SYMBOL	mm	
	MIN	MAX
A	4.5	4.9
B	1.22	1.47
b	0.7	0.9
c	0.45	0.60
D	15.6	16.1
D1	9.0	9.3
e	2.54TYPE	
E	9.9	10.4
F	2.3	2.8
L	12.6	13.3
L1	3.1	3.4
Q	3.2	3.4
Q1	2.6	2.9
ΦP	3.0	3.5



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